NXP USA Inc. - MPC8321CVRAFDCA Datasheet

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8321cvrafdca

1.1.2 Serial Interfaces

The MPC8323E serial interfaces are as follows:

- Support for one UL2 interface with 31 multi-PHY addresses (MPC8323E and MPC8323 only)
- Support for up to three 10/100 Mbps Ethernet interfaces using MII or RMII
- Support for up to four T1/E1/J1/E3 or DS-3 serial interfaces (TDM)
- Support for dual UART and SPI interfaces and a single I^{2}C interface

1.2 QUICC Engine Block

The QUICC Engine block is a versatile communications complex that integrates several communications peripheral controllers. It provides on-chip system design for a variety of applications, particularly in communications and networking systems. The QUICC Engine block has the following features:

- One 32-bit RISC controller for flexible support of the communications peripherals
- Serial DMA channel for receive and transmit on all serial channels
- Five universal communication controllers (UCCs) supporting the following protocols and interfaces (not all of them simultaneously):
  - 10/100 Mbps Ethernet/IEEE 802.3® standard
  - IP support for IPv4 and IPv6 packets including TOS, TTL, and header checksum processing
  - ATM protocol through UTOPIA interface (note that the MPC8321 and MPC8321E do not support the UTOPIA interface)
  - HDLC /transparent up to 70-Mbps full-duplex
  - HDLC bus up to 10 Mbps
  - Asynchronous HDLC
  - UART
  - BISYNC up to 2 Mbps
  - QUICC multi-channel controller (QMC) for 64 TDM channels
- One UTOPIA interface (UPC1) supporting 31 multi-PHYs (MPC8323E- and MPC8323-specific)
- Two serial peripheral interfaces (SPI). SPI2 is dedicated to Ethernet PHY management.
- Four TDM interfaces
- Thirteen independent baud rate generators and 19 input clock pins for supplying clocks to UCC serial channels
- Four independent 16-bit timers that can be interconnected as two 32-bit timers

The UCCs are similar to the PowerQUICC II peripherals: SCC (BISYNC, UART, and HDLC bus) and FCC (fast Ethernet, HDLC, transparent, and ATM).

Table 7. CLKIN DC Electrical Characteristics (continued)

CLKIN input current	0 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	±5	μA
PCI_SYNC_IN input current	0 V ≤ V_{IN} ≤ 0.5 V or OV_{DD} – 0.5 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	±5	μA
PCI_SYNC_IN input current	0.5 V ≤ V_{IN} ≤ OV_{DD} – 0.5 V	I_{IN}	—	±50	μA

4.2 AC Electrical Characteristics

The primary clock source for the MPC8323E can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 8 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the MPC8323E.

Table 8. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	25	—	66.67	MHz	1
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN rise and fall time	t_{KH}, t_{KL}	0.6	0.8	4	ns	2
PCI_CLK rise and fall time	t_{PCH}, t_{PCL}	0.6	0.8	1.2	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The system, core, security, and QUICC Engine block must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be < 500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.

5 RESET Initialization

This section describes the AC electrical specifications for the reset initialization timing requirements of the MPC8323E. Table 9 provides the reset initialization AC timing specifications for the reset component(s).

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$ or $\overline{\text{SRESET}}$ (input) to activate reset flow	32	—	$t_{PCI\_SYNC\_IN}$	1
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to CLKIN when the MPC8323E is in PCI host mode	32	—	t_{CLKIN}	2
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to PCI_SYNC_IN when the MPC8323E is in PCI agent mode	32	—	$t_{PCI\_SYNC\_IN}$	1

Figure 4 shows the input timing diagram for the DDR controller.

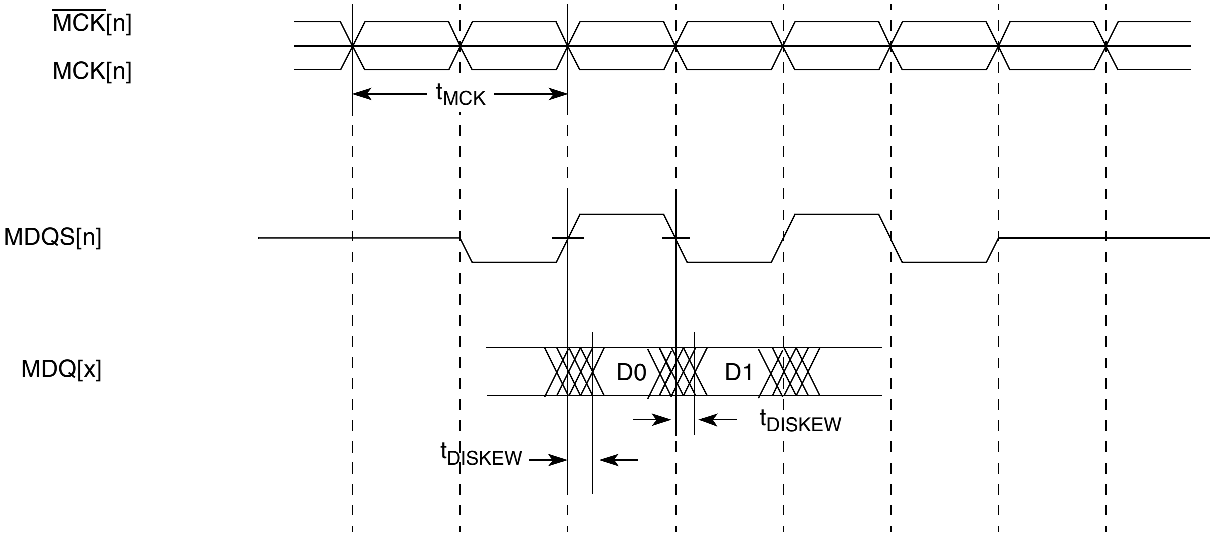


Figure 4. DDR Input Timing Diagram

6.2.2 DDR1 and DDR2 SDRAM Output AC Timing Specifications

Table 19 provides the output AC timing specifications for the DDR1 and DDR2 SDRAM interfaces.

Table 19. DDR1 and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with D*n*_GV$_{DD}$ of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MCK cycle time, (MCK/$\overline{\text{MCK}}$ crossing)	t_{MCK}	7.5	10	ns	2
ADDR/CMD output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHAS}	 2.5 3.5	 — —	ns	3
ADDR/CMD output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHAX}	 2.5 3.5	 — —	ns	3
$\overline{\text{MCS}}$ output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHCS}	 2.5 3.5	 — —	ns	3
$\overline{\text{MCS}}$ output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHCX}	 2.5 3.5	 — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4

Table 19. DDR1 and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with D*n*_GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQ/MDM output setup with respect to MDQS 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 0.9 1.0	 — —	ns	5
MDQ/MDM output hold with respect to MDQS 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 1100 1200	 — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the Clock Control register is set to adjust the memory clocks by 1/2 applied cycle.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK(n) at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

8.3.1 MII Management DC Electrical Characteristics

MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 27.

Table 27. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	$I_{OH} = –1.0$ mA	OV_{DD} = Min	2.10	$OV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0$ mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±5	μA

8.3.2 MII Management AC Electrical Specifications

Table 28 provides the MII management AC timing specifications.

Table 28. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	—
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	—
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—
MDC fall time	t_{MDHF}	—	—	10	ns	—

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Table 30. Local Bus General Timing Parameters (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock (LCLK*n*) to output valid	t_{LBKHOV}	—	3	ns	3
Local bus clock (LCLK*n*) to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8
Local bus clock (LCLK*n*) duty cycle	t_{LBDC}	47	53	%	—
Local bus clock (LCLK*n*) jitter specification	t_{LBRJ}	—	400	ps	—
Delay between the input clock (PCI_SYNC_IN) of local bus output clock (LCLK*n*)	t_{LBCDL}	—	1.7	ns	—

Notes:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1).
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

Figure 14 provides the AC test load for the local bus.

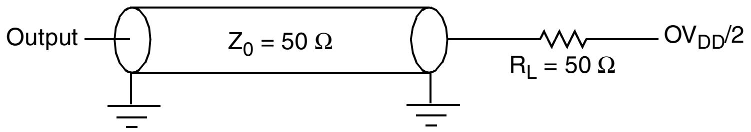


Figure 14. Local Bus C Test Load

11 I^{2}C

This section describes the DC and AC electrical characteristics for the I^{2}C interface of the MPC8323E.

11.1 I^{2}C DC Electrical Characteristics

Table 33 provides the DC electrical characteristics for the I^{2}C interface of the MPC8323E.

Table 33. I^{2}C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	0.4	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Capacitance for each I/O pin	C_I	—	10	pF	—
Input current ($0 V \le V_{IN} \le OV_{DD}$)	I_{IN}	—	±5	μA	4

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for information on the digital filter used.
4. I/O pins obstructs the SDA and SCL lines if OV_{DD} is switched off.

11.2 I^{2}C AC Electrical Specifications

Table 34 provides the AC timing parameters for the I^{2}C interface of the MPC8323E.

Table 34. I^{2}C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 33).

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns
Data hold time: CBUS compatible masters I^{2}C bus devices	t_{I2DXKL}	— 0[2]	— 0.9[3]	μs

Table 34. I^2C AC Electrical Specifications (continued)

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 33).

Parameter	Symbol[1]	Min	Max	Unit
Rise time of both SDA and SCL signals	t_{I2CR}	$20 + 0.1\ C_b$[4]	300	ns
Fall time of both SDA and SCL signals	t_{I2CF}	$20 + 0.1\ C_b$[4]	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I^2C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I^2C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I^2C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. MPC8323E provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH}(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

Figure 23 provides the AC test load for the I^2C.

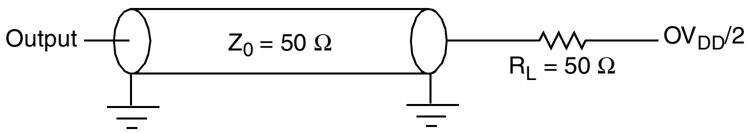


Figure 23. I^2C AC Test Load

Figure 24 shows the AC timing diagram for the I^2C bus.

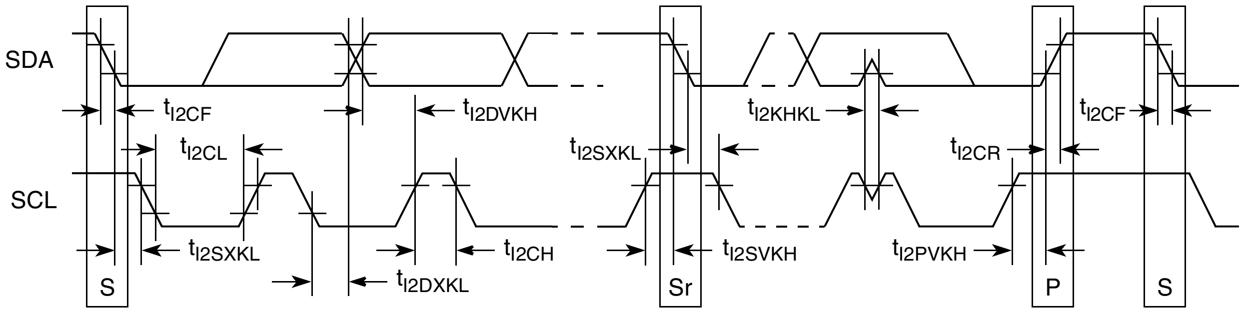


Figure 24. I^2C Bus AC Timing Diagram

12 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8323E.

12.1 PCI DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the PCI interface of the MPC8323E.

Table 35. PCI DC Electrical Characteristics[1,2]

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	–0.3	0.8	V
High-level output voltage	V_{OH}	OV_{DD} = min, I_{OH} = –100 μA	OV_{DD} – 0.2	—	V
Low-level output voltage	V_{OL}	OV_{DD} = min, I_{OL} = 100 μA	—	0.2	V
Input current	I_{IN}	$0 V \leq V_{IN} \leq OV_{DD}$	—	±5	μA

Notes:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.
2. Ranges listed do not meet the full range of the DC specifications of the *PCI 2.3 Local Bus Specifications*.

12.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus of the MPC8323E. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the MPC8323E is configured as a host or agent device. Table 36 shows the PCI AC timing specifications at 66 MHz.

Table 36. PCI AC Timing Specifications at 66 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	6.0	ns	2
Output hold from clock	t_{PCKHOX}	1	—	ns	2
Clock to output high impedence	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0	—	ns	2, 4

Notes:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

19 HDLC, BISYNC, Transparent, and Synchronous UART

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), BISYNC, transparent, and synchronous UART of the MPC8323E.

19.1 HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Table 50 provides the DC electrical characteristics for the MPC8323E HDLC, BISYNC, transparent, and synchronous UART protocols.

Table 50. HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -2.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	±5	μA

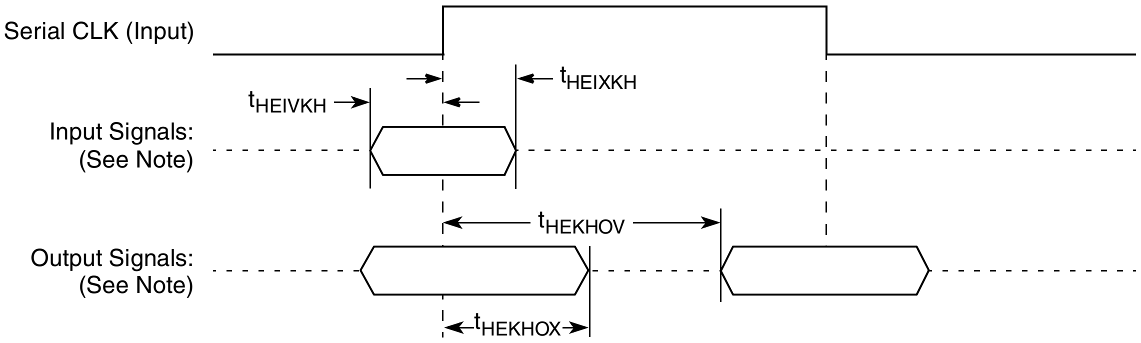
19.2 HDLC, BISYNC, Transparent, and Synchronous UART AC Timing Specifications

Table 51 provides the input and output AC timing specifications for HDLC, BISYNC, and transparent UART protocols.

Table 51. HDLC, BISYNC, and Transparent UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	t_{HIKHOV}	0	5.5	ns
Outputs—External clock delay	t_{HEKHOV}	1	10	ns
Outputs—Internal clock high impedance	t_{HIKHOX}	0	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	6	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	0	—	ns

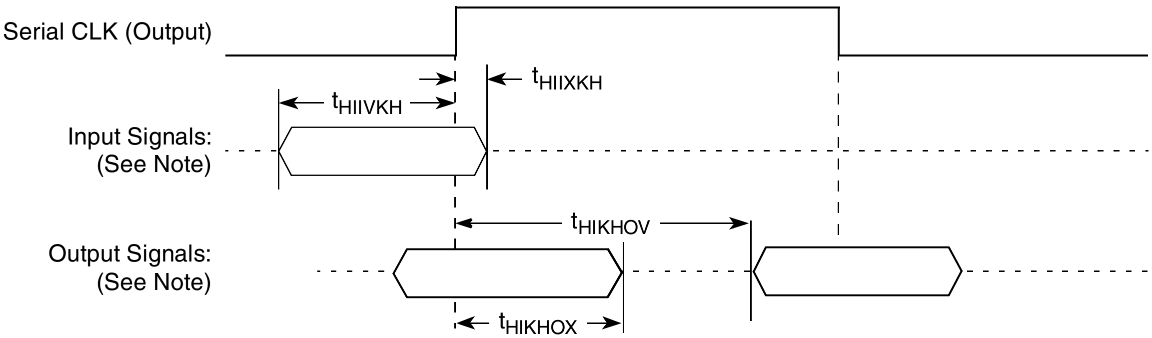
Figure 39 shows the timing with external clock.



Note: The clock edge is selectable.

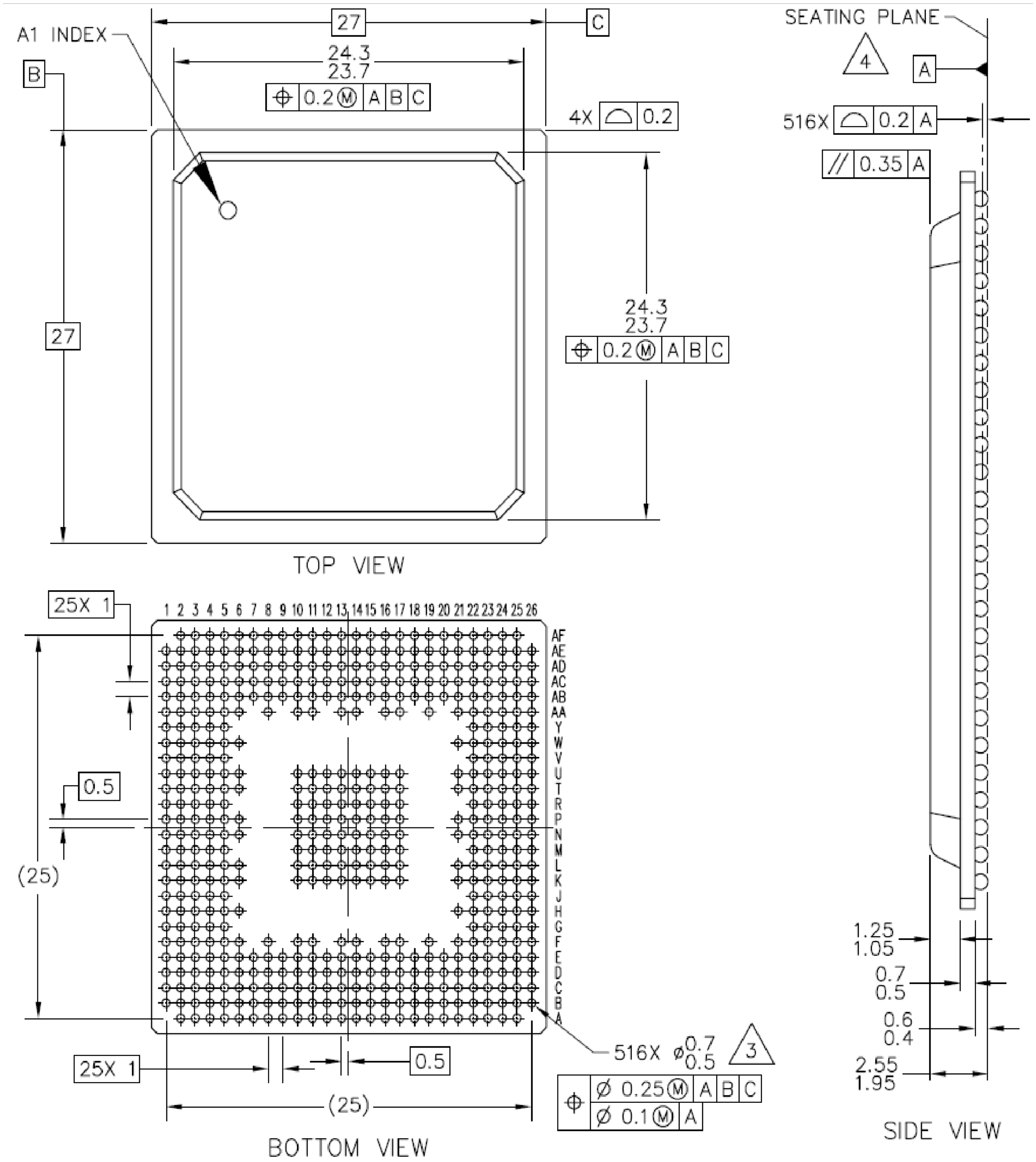
Figure 39. AC Timing (External Clock) Diagram

Figure 40 shows the timing with internal clock.



Note: The clock edge is selectable.

Figure 40. AC Timing (Internal Clock) Diagram



Notes:

1.All dimensions are in millimeters.

2.Dimensions and tolerances per ASME Y14.5M-1994.

3.Maximum solder ball diameter measured parallel to datum A.

4.Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Figure 42. Mechanical Dimensions and Bottom Surface Nomenclature of the MPC8323E PBGA

21.3 Pinout Listings

Table 55 shows the pin list of the MPC8323E.

Table 55. MPC8323E PBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DDR Memory Controller Interface				
MEMC_MDQ0	AE9	IO	GV_{DD}	—
MEMC_MDQ1	AD10	IO	GV_{DD}	—
MEMC_MDQ2	AF10	IO	GV_{DD}	—
MEMC_MDQ3	AF9	IO	GV_{DD}	—
MEMC_MDQ4	AF7	IO	GV_{DD}	—
MEMC_MDQ5	AE10	IO	GV_{DD}	—
MEMC_MDQ6	AD9	IO	GV_{DD}	—
MEMC_MDQ7	AF8	IO	GV_{DD}	—
MEMC_MDQ8	AE6	IO	GV_{DD}	—
MEMC_MDQ9	AD7	IO	GV_{DD}	—
MEMC_MDQ10	AF6	IO	GV_{DD}	—
MEMC_MDQ11	AC7	IO	GV_{DD}	—
MEMC_MDQ12	AD8	IO	GV_{DD}	—
MEMC_MDQ13	AE7	IO	GV_{DD}	—
MEMC_MDQ14	AD6	IO	GV_{DD}	—
MEMC_MDQ15	AF5	IO	GV_{DD}	—
MEMC_MDQ16	AD18	IO	GV_{DD}	—
MEMC_MDQ17	AE19	IO	GV_{DD}	—
MEMC_MDQ18	AF17	IO	GV_{DD}	—
MEMC_MDQ19	AF19	IO	GV_{DD}	—
MEMC_MDQ20	AF18	IO	GV_{DD}	—
MEMC_MDQ21	AE18	IO	GV_{DD}	—
MEMC_MDQ22	AF20	IO	GV_{DD}	—
MEMC_MDQ23	AD19	IO	GV_{DD}	—
MEMC_MDQ24	AD21	IO	GV_{DD}	—
MEMC_MDQ25	AF22	IO	GV_{DD}	—
MEMC_MDQ26	AC21	IO	GV_{DD}	—
MEMC_MDQ27	AF21	IO	GV_{DD}	—
MEMC_MDQ28	AE21	IO	GV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_AD20	AB2	IO	OV_{DD}	—
PCI_AD21	Y4	IO	OV_{DD}	—
PCI_AD22	AC1	IO	OV_{DD}	—
PCI_AD23	AA3	IO	OV_{DD}	—
PCI_AD24	AA4	IO	OV_{DD}	—
PCI_AD25	AD1	IO	OV_{DD}	—
PCI_AD26	AD2	IO	OV_{DD}	—
PCI_AD27	AB3	IO	OV_{DD}	—
PCI_AD28	AB4	IO	OV_{DD}	—
PCI_AD29	AE1	IO	OV_{DD}	—
PCI_AD30	AC3	IO	OV_{DD}	—
PCI_AD31	AC4	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE0}}$	M4	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE1}}$	T4	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE2}}$	Y3	IO	OV_{DD}	—
PCI_C_$\overline{\text{BE3}}$	AC2	IO	OV_{DD}	—
PCI_PAR	U3	IO	OV_{DD}	—
$\overline{\text{PCI\_FRAME}}$	W1	IO	OV_{DD}	5
$\overline{\text{PCI\_TRDY}}$	W4	IO	OV_{DD}	5
$\overline{\text{PCI\_IRDY}}$	W2	IO	OV_{DD}	5
$\overline{\text{PCI\_STOP}}$	V4	IO	OV_{DD}	5
$\overline{\text{PCI\_DEVSEL}}$	W3	IO	OV_{DD}	5
PCI_IDSEL	P2	I	OV_{DD}	—
$\overline{\text{PCI\_SERR}}$	U4	IO	OV_{DD}	5
$\overline{\text{PCI\_PERR}}$	V3	IO	OV_{DD}	5
$\overline{\text{PCI\_REQ0}}$	AD4	IO	OV_{DD}	—
$\overline{\text{PCI\_REQ1}}$/CPCI_HS_ES	AE3	I	OV_{DD}	—
$\overline{\text{PCI\_REQ2}}$	AF3	I	OV_{DD}	—
$\overline{\text{PCI\_GNT0}}$	AD3	IO	OV_{DD}	—
$\overline{\text{PCI\_GNT1}}$/CPCI_HS_LED	AE4	O	OV_{DD}	—
$\overline{\text{PCI\_GNT2}}$/CPCI_HS_ENUM	AF4	O	OV_{DD}	—
M66EN	L4	I	OV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
CE/GPIO				
GPIO_PA0/SER1_TXD[0]/TDMA_TXD[0]/USBTXN	G3	IO	OV_{DD}	—
GPIO_PA1/SER1_TXD[1]/TDMA_TXD[1]/USBTXP	F3	IO	OV_{DD}	—
GPIO_PA2/SER1_TXD[2]/TDMA_TXD[2]	F2	IO	OV_{DD}	—
GPIO_PA3/SER1_TXD[3]/TDMA_TXD[3]	E3	IO	OV_{DD}	—
GPIO_PA4/SER1_RXD[0]/TDMA_RXD[0]/USBRXP	E2	IO	OV_{DD}	—
GPIO_PA5/SER1_RXD[1]/TDMA_RXD[1]/USBRXN	E1	IO	OV_{DD}	—
GPIO_PA6/SER1_RXD[2]/TDMA_RXD[2]/USBRXD	D3	IO	OV_{DD}	—
GPIO_PA7/SER1_RXD[3]/TDMA_RXD[3]	D2	IO	OV_{DD}	—
GPIO_PA8/SER1_CD/TDMA_REQ/$\overline{\text{USBOE}}$	D1	IO	OV_{DD}	—
GPIO_PA9 TDMA_CLKO	C3	IO	OV_{DD}	—
GPIO_PA10/SER1_CTS/TDMA_RSYNC	C2	IO	OV_{DD}	—
GPIO_PA11/TDMA_STROBE	C1	IO	OV_{DD}	—
GPIO_PA12/SER1_RTS/TDMA_TSYNC	B1	IO	OV_{DD}	—
GPIO_PA13/CLK9/BRGO9	H4	IO	OV_{DD}	—
GPIO_PA14/CLK11/BRGO10	G4	IO	OV_{DD}	—
GPIO_PA15/BRGO7	J4	IO	OV_{DD}	—
GPIO_PA16/ LA0 (LBIU)	K24	IO	OV_{DD}	—
GPIO_PA17/ LA1 (LBIU)	K26	IO	OV_{DD}	—
GPIO_PA18/Enet2_TXD[0]/SER2_TXD[0]/ TDMB_TXD[0]/LA2 (LBIU)	G25	IO	OV_{DD}	—
GPIO_PA19/Enet2_TXD[1]/SER2_TXD[1]/ TDMB_TXD[1]/LA3 (LBIU)	G26	IO	OV_{DD}	—
GPIO_PA20/Enet2_TXD[2]/SER2_TXD[2]/ TDMB_TXD[2]/LA4 (LBIU)	H25	IO	OV_{DD}	—
GPIO_PA21/Enet2_TXD[3]/SER2_TXD[3]/ TDMB_TXD[3]/LA5 (LBIU)	H26	IO	OV_{DD}	—
GPIO_PA22/Enet2_RXD[0]/SER2_RXD[0]/ TDMB_RXD[0]/LA6 (LBIU)	C25	IO	OV_{DD}	—
GPIO_PA23/Enet2_RXD[1]/SER2_RXD[1]/ TDMB_RXD[1]/LA7 (LBIU)	C26	IO	OV_{DD}	—
GPIO_PA24/Enet2_RXD[2]/SER2_RXD[2]/ TDMB_RXD[2]/LA8 (LBIU)	D25	IO	OV_{DD}	—
GPIO_PA25/Enet2_RXD[3]/SER2_RXD[3]/ TDMB_RXD[3]/LA9 (LBIU)	D26	IO	OV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO_PD10/GTM1_TIN2/GTM2_TIN1/CLK17	J24	IO	OV_{DD}	—
GPIO_PD11/$\overline{\text{GTM1\_TGATE2}}$/$\overline{\text{GTM2\_TGATE1}}$	B25	IO	OV_{DD}	—
GPIO_PD12/$\overline{\text{GTM1\_TOUT2}}$/$\overline{\text{GTM2\_TOUT1}}$	C4	IO	OV_{DD}	—
GPIO_PD13/GTM1_TIN3/GTM2_TIN4/BRGO8	D4	IO	OV_{DD}	—
GPIO_PD14/$\overline{\text{GTM1\_TGATE3}}$/$\overline{\text{GTM2\_TGATE4}}$	D5	IO	OV_{DD}	—
GPIO_PD15/$\overline{\text{GTM1\_TOUT3}}$	A5	IO	OV_{DD}	—
GPIO_PD16/GTM1_TIN4/GTM2_TIN3	B5	IO	OV_{DD}	—
GPIO_PD17/$\overline{\text{GTM1\_TGATE4}}$/$\overline{\text{GTM2\_TGATE3}}$	C5	IO	OV_{DD}	—
GPIO_PD18/$\overline{\text{GTM1\_TOUT4}}$/$\overline{\text{GTM2\_TOUT3}}$	A6	IO	OV_{DD}	—
GPIO_PD19/CE_RISC1_INT/CE_EXT_REQ4	B6	IO	OV_{DD}	—
GPIO_PD20/CLK18/BRGO6	D21	IO	OV_{DD}	—
GPIO_PD21/CLK16/BRGO5/UPC1_CLKO	C19	IO	OV_{DD}	—
GPIO_PD22/CLK4/BRGO9/UCC2_CLKO	A7	IO	OV_{DD}	—
GPIO_PD23/CLK3/BRGO10/UCC3_CLKO	B7	IO	OV_{DD}	—
GPIO_PD24/CLK10/BRGO2/UCC4_CLKO	A12	IO	OV_{DD}	—
GPIO_PD25/CLK13/BRGO16/UCC5_CLKO	B10	IO	OV_{DD}	—
GPIO_PD26/CLK2/BRGO4/UCC1_CLKO	E4	IO	OV_{DD}	—
GPIO_PD27/CLK1/BRGO3	F4	IO	OV_{DD}	—
GPIO_PD28/CLK19/BRGO11	D15	IO	OV_{DD}	—
GPIO_PD29/CLK15/BRGO8	C6	IO	OV_{DD}	—
GPIO_PD30/CLK14	D6	IO	OV_{DD}	—
GPIO_PD31/CLK7/BRGO15	E24	IO	OV_{DD}	—
Power and Ground Supplies				
GV_{DD}	AA8, AA10, AA11, AA13, AA14, AA16, AA17, AA19, AA21, AB9, AB10, AB11, AB12, AB14, AB18, AB20, AB21, AC6, AC8, AC14, AC18	GV_{DD}	—	—
OV_{DD}	E5, E6, E8, E9, E10, E12, E14, E15, E16, E18, E19, E20, E22, F5, F6, F8, F10, F14, F16, F19, F22, G22, H5, H6, H21, J5, J22, K21, K22, L5, L6, L22, M5, M22, N5, N21, N22, P6, P22, P23, R5, R23, T5, T21, T22, U6, U22, V5, V22, W22, Y5, AB5, AB6, AC5	OV_{DD}	—	—

22 Clocking

Figure 43 shows the internal distribution of clocks within the MPC8323E.

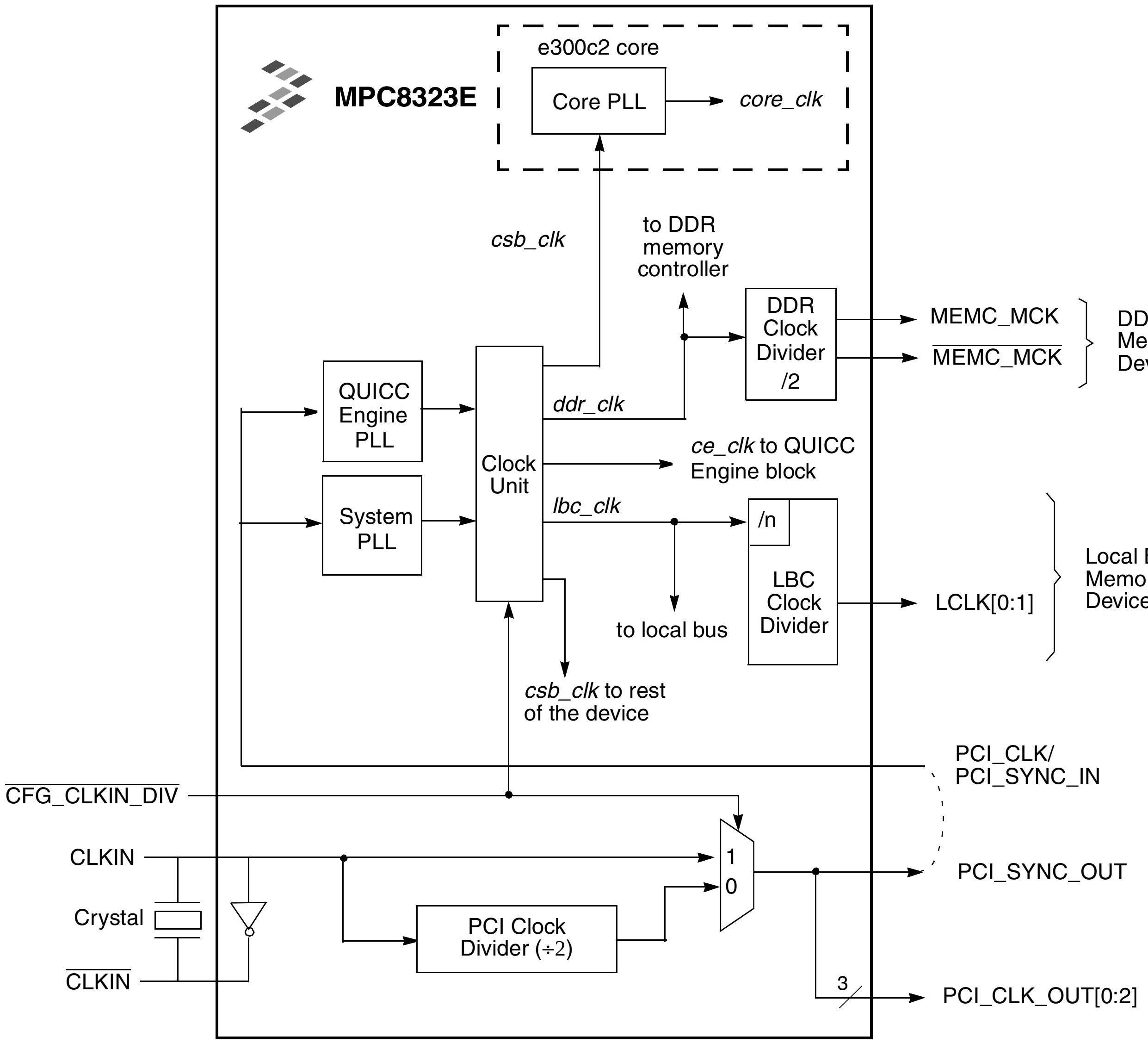


Figure 43. MPC8323E Clock Subsystem

The primary clock source for the MPC8323E can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode, respectively.

22.5 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 60 shows the encodings for RCWL[COREPLL]. COREPLL values not listed in Table 60 should be considered reserved.

Table 60. e300 Core PLL Configuration

RCWL[COREPLL]			***core_clk* : *csb_clk* Ratio**	**VCO Divider**
0-1	**2-5**	**6**		
nn	**0000**	n	PLL bypassed (PLL off, *csb_clk* clocks core directly)	PLL bypassed (PLL off, *csb_clk* clocks core directly)
00	**0001**	0	1:1	÷2
01	**0001**	0	1:1	÷4
10	**0001**	0	1:1	÷8
11	**0001**	0	1:1	÷8
00	**0001**	1	1.5:1	÷2
01	**0001**	1	1.5:1	÷4
10	**0001**	1	1.5:1	÷8
11	**0001**	1	1.5:1	÷8
00	**0010**	0	2:1	÷2
01	**0010**	0	2:1	÷4
10	**0010**	0	2:1	÷8
11	**0010**	0	2:1	÷8
00	**0010**	1	2.5:1	÷2
01	**0010**	1	2.5:1	÷4
10	**0010**	1	2.5:1	÷8
11	**0010**	1	2.5:1	÷8
00	**0011**	0	3:1	÷2
01	**0011**	0	3:1	÷4
10	**0011**	0	3:1	÷8
11	**0011**	0	3:1	÷8

NOTE

Core VCO frequency = core frequency × VCO divider

VCO divider (RCWL[COREPLL[0:1]]) must be set properly so that the core VCO frequency is in the range of 500–800 MHz.

Table 64. Package Thermal Characteristics for PBGA (continued)

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-package top	Natural convection	Ψ_{JT}	2	°C/W	6

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

23.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$, where $P_{I/O}$ is the power dissipation of the I/O drivers.

23.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)
T_A = ambient temperature for the package (°C)
$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

23.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

T_J = junction temperature (°C)

T_B = board temperature at the package perimeter (°C)

$R_{\theta JB}$ = junction-to-board thermal resistance (°C/W) per JESD51-8

P_D = power dissipation in package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

23.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the thermal characterization parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = thermal characterization parameter (°C/W)

P_D = power dissipation in package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

23.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

In some application environments, a heat sink is required to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$